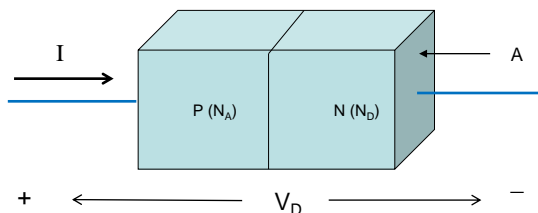


Ecuación de la Juntura P - N



Depende de la polarización

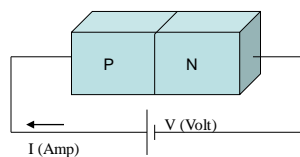
$$I = I_s \left[e^{(V_D/U_T)} - 1 \right]$$

Depende de la fabricación

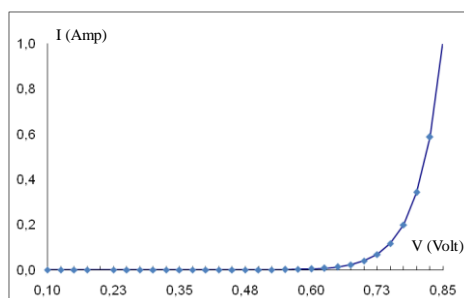
$$I_s = qn_i^2 A \left[\frac{D_p}{L_p N_D} + \frac{D_n}{L_n N_A} \right]$$

CARACTERISTICA V- I JUNTURA P-N

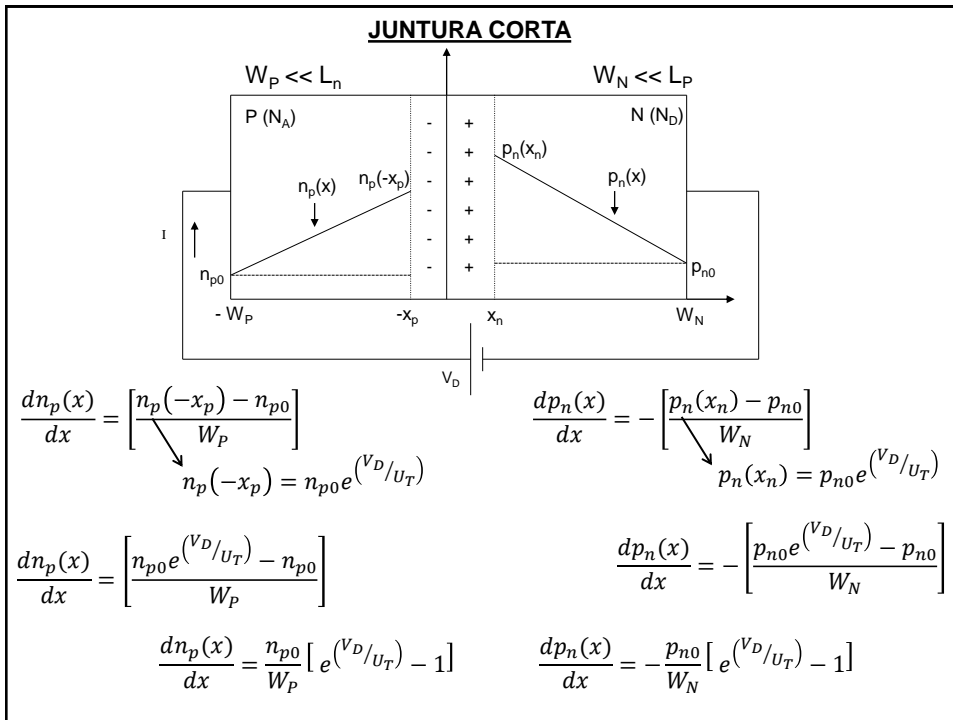
$$I_s = 1,1 \times 10^{-8}$$



$$I = I_s \left[\exp(V_D/U_T) - 1 \right]$$



V	I
0.1	8.39E-08
0.125	1.52E-07
0.15	2.69E-07
0.175	4.69E-07
0.2	8.09E-07
0.225	1.40E-06
0.25	2.40E-06
0.275	4.19E-06
0.3	7.09E-06
0.325	1.22E-05
0.35	2.09E-05
0.375	3.59E-05
0.4	6.19E-05
0.425	1.05E-04
0.45	1.80E-04
0.475	3.09E-04
0.5	5.30E-04
0.525	9.09E-04
0.55	1.59E-03
0.575	2.67E-03
0.6	4.59E-03
0.625	7.89E-03
0.65	1.35E-02
0.675	2.31E-02
0.7	3.95E-02
0.725	6.79E-02
0.75	1.17E-01
0.775	2.00E-01
0.8	3.43E-01
0.825	5.87E-01
0.85	1.00E+00



$$J_{Dn}(x) = q D_n \frac{dn_p(x)}{dx} \quad J_{Dp}(x) = -q D_p \frac{dp_n(x)}{dx}$$

$$J_{Dn}(x) = \frac{q D_n n_{p0}}{W_p} [e^{(V_D/U_T)} - 1] \quad J_{Dp}(x) = \frac{q D_p p_{n0}}{W_n} [e^{(V_D/U_T)} - 1]$$

$$J_T = \left[\frac{q D_n n_{p0}}{W_p} + \frac{q D_p p_{n0}}{W_n} \right] [e^{(V_D/U_T)} - 1]$$

$$I_T = qA \left[\frac{D_n n_{p0}}{W_p} + \frac{D_p p_{n0}}{W_n} \right] [e^{(V_D/U_T)} - 1]$$

$$I_T = I_S [e^{(V_D/U_T)} - 1]$$

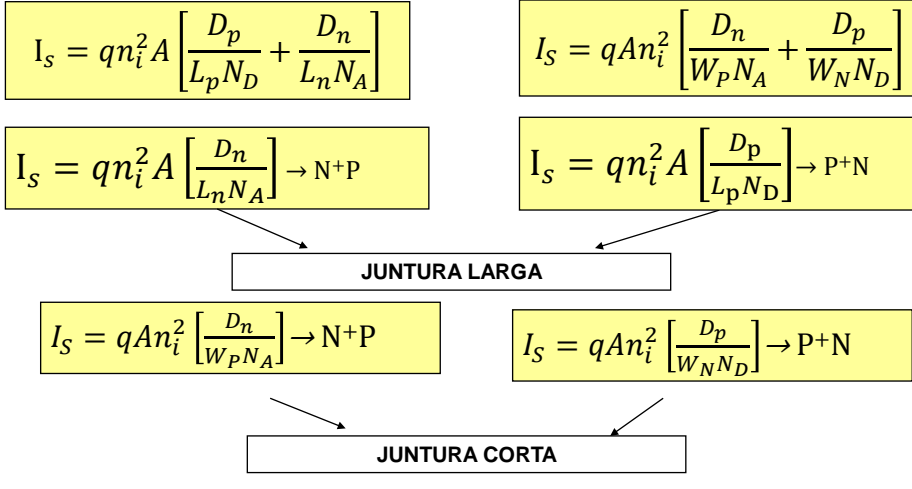
$$I_S = qA \left[\frac{D_n n_{p0}}{W_p} + \frac{D_p p_{n0}}{W_n} \right]$$

$$I_S = qA n_i^2 \left[\frac{D_n}{W_p N_A} + \frac{D_p}{W_n N_D} \right]$$

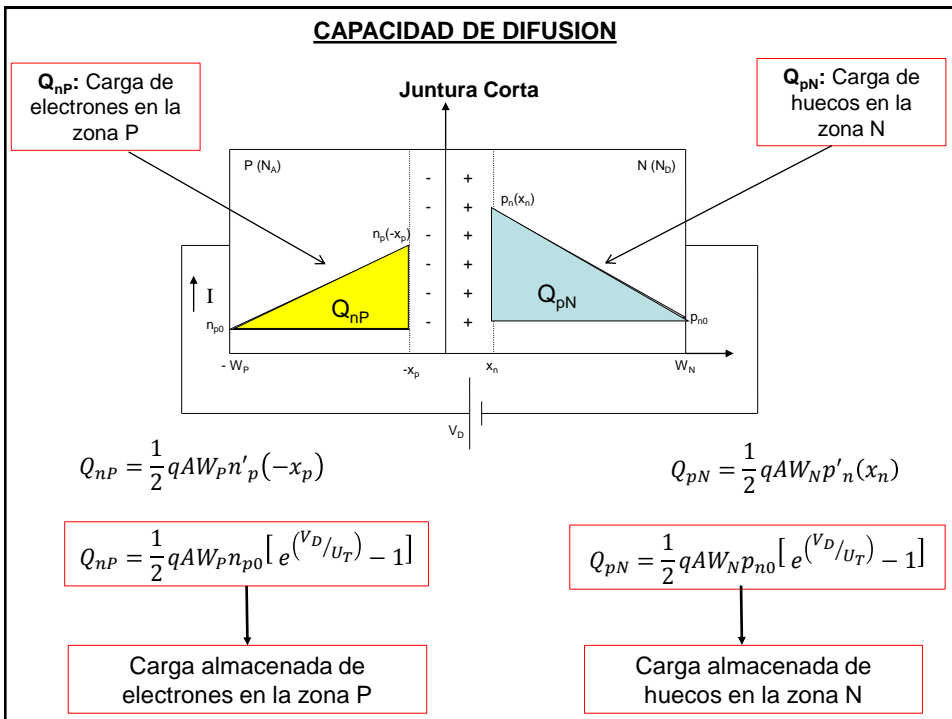
I_S Para Juntura Corta

JUNTURA ASIMETRICA

- Cuando una de las zonas (N o P) tiene muchas mas impurezas que la otra
 - N+ P $N_D \gg N_A$
 - P+ N $N_A \gg N_D$
- En estas condiciones el parámetro IS esta determinado por la zona menos contaminada



CAPACIDAD DE DIFUSION



Suponiendo una Juntura P+N \longrightarrow $Q_{nP} \ll Q_{pN}$

$$Q_{pN} = \frac{1}{2} q A W_N p_{n0} [e^{(V_D/U_T)} - 1]$$

$$I = \frac{q A D_p p_{n0}}{W_N} [e^{(V_D/U_T)} - 1]$$

$$\frac{Q_{pN}}{I} = \frac{W_N^2}{2 D_p}$$

$$\frac{Q_{pN}}{I} = T_T$$

$T_T \rightarrow$ Tiempo de transito

Tiempo de Transito: Tiempo que demora un hueco en atravesar la zona P

$Q = T_T I$ Capacidad [C] $\longrightarrow C = \frac{dQ}{dV} \longrightarrow \frac{dQ}{dV} = T_T \frac{dI}{dV} \longrightarrow \frac{dI}{dV} = \frac{I}{U_T}$

$$C_D = T_T \frac{I}{U_T} \quad I = I_S [e^{(V_D/U_T)} - 1]$$

CAPACIDAD DE DIFUSION

Juntura Larga

- Carga almacenada en las zonas neutras con polarización directa

$Q_{pN} \rightarrow$ Carga de huecos en la zona N

Para una juntura P+N $Q_{pN} \gg Q_{nP}$

$$Q_{pN} = qA \int_{x_n}^{W_N} p'_n(x) dx \quad Q_{pN} = qA \int_{x_n}^{W_N} (p_n(x_n) - p_{n0}) e^{\left(\frac{-x+x_n}{L_p}\right)} dx$$

$$Q_{pN} = q A L_p [p_n(x_n) - p_{n0}]$$

$$Q_{pN} = q A L_p p_{n0} [e^{(V_D/U_T)} - 1]$$

$$I = \frac{q A D_p p_{n0}}{L_p} [e^{(V_D/U_T)} - 1]$$

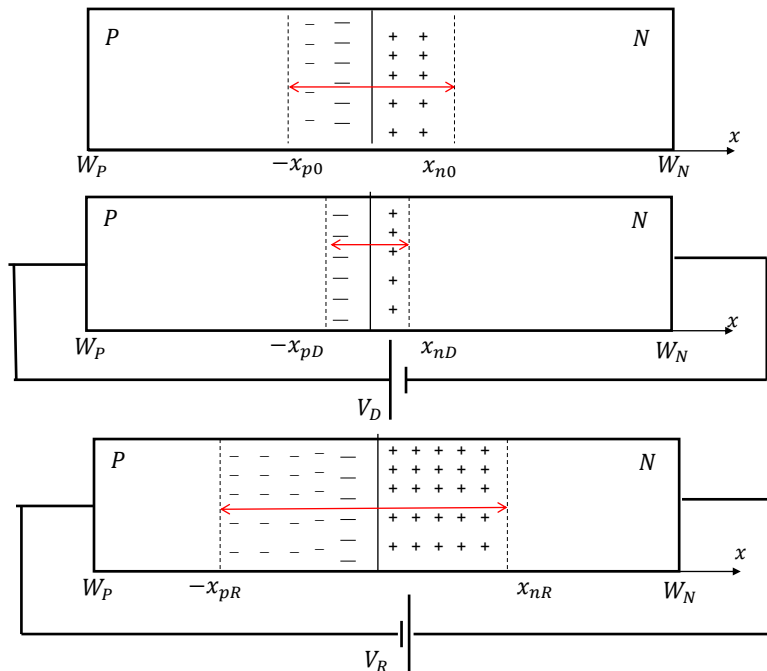
$$\frac{Q_{pN}}{I} = \frac{L_p^2}{D_p} = \tau_p \rightarrow \text{tiempo de vida medio de los huecos}$$

$$Q = \tau_p I \quad I = I_S [e^{(V_D/U_T)} - 1]$$

$$\text{Capacidad [C]} \quad C = \frac{dQ}{dV} \rightarrow \frac{dQ}{dV} = \tau_p \frac{dI}{dV} \rightarrow \frac{dI}{dV} = \frac{I}{U_T}$$

$$C_D = \tau_p \frac{I}{U_T}$$

Ancho de la zona de Deplexion vs. Tensión aplicada a la Juntura



$x_m = x_n + x_p$

$x_{m0} \rightarrow$ ancho de la zona de deplexion sin polarización $V_D = 0$
 $x_m < x_{m0} \rightarrow$ para polarización directa $V_D > 0$
 $x_m > x_{m0} \rightarrow$ para polarización inversa $V_D < 0$

El ancho de la zona de deplexion varia con la tensión aplicada a la juntura

$C_j = \epsilon \frac{A}{x_m}$

\longrightarrow Capacidad de la zona de deplexion

$\epsilon = 1,04 \times 10^{-12} \left[\frac{F}{cm} \right]$

$C_j \rightarrow f(x_m) \longrightarrow x_m \rightarrow f(V_D) \longrightarrow$
 $C_j \rightarrow$ Capacitor variable con tensión

Buscamos la función $x_m(V_D)$ para obtener $C_j(V_D)$

$\frac{d^2V}{dx^2} = -\frac{\rho}{\epsilon}$ $\rho \rightarrow$ densidad de carga
 $\epsilon \rightarrow$ constante dielectrica del silicio

Ecuación de Poisson

$E(x) = -\frac{dV}{dx}$

$x_p N_A = x_n N_D$

Ecuación de Poisson para una dimensión $\longrightarrow \frac{d^2V}{dx^2} = -\frac{\rho}{\epsilon}$ $\rho \rightarrow$ densidad de carga
 $\epsilon \rightarrow$ constante dielectrica del silicio

$$\frac{d^2V}{dx^2} = \frac{qN_A}{\epsilon} \rightarrow -x_p < x < 0$$

Integrando $\frac{d^2V}{dx^2}$ respecto de x obtengo $\frac{dV}{dx} \longrightarrow \frac{dV}{dx} = \frac{qN_A x}{\epsilon} + C_1$

Condicion de borde $\frac{dV}{dx} = 0 \rightarrow x = -x_p \longrightarrow C_1 = \frac{qN_A x_p}{\epsilon}$

$$\frac{dV}{dx} = \frac{qN_A(x + x_p)}{\epsilon} \longrightarrow -x_p < x < 0$$

$$E(x) = -\frac{dV}{dx} = -\frac{qN_A(x + x_p)}{\epsilon} \longrightarrow -x_p < x < 0$$

$$|E_{max}| = |E(0)| = \frac{qN_A x_p}{\epsilon}$$

Integrando $\frac{dV}{dx}$ obtengo $\longrightarrow V(x) = \frac{qN_A}{\epsilon} \left(\frac{x^2}{2} + x \times x_p \right) + C_2 \rightarrow -x_p < x < 0$

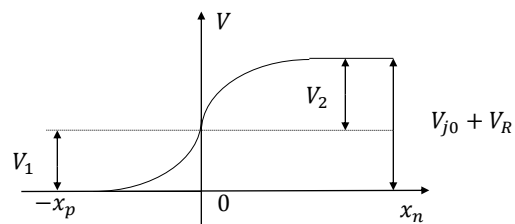
Condicion de borde $V(-x_p) = 0 \longrightarrow C_2 = \frac{qN_A x_p^2}{2\epsilon}$

$$V(x) = \frac{qN_A}{2\epsilon} (x + x_p)^2 \rightarrow -x_p < x < 0$$

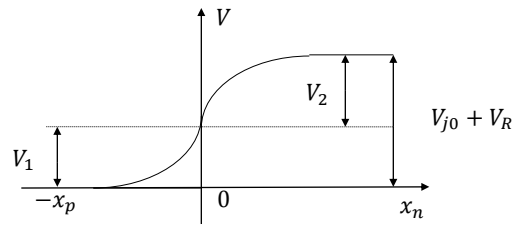
$$V_1 = V(0) = \frac{qN_A x_p^2}{2\epsilon}$$

Analizando entre $0 < x < x_n \longrightarrow V_2 = V(x_n) = \frac{qN_D x_n^2}{2\epsilon}$

$$V_1 + V_2 = V_{j0} + V_R = -V_{j0} + V_D$$



$$V_1 + V_2 = V_{j0} + V_R = -V_{j0} + V_D$$



$$V_{j0} + V_R = \frac{q}{2\varepsilon} (N_D x_n^2 + N_A x_p^2)$$

$$V_{j0} + V_R = \frac{q x_p^2 N_A}{2\varepsilon} \left(\frac{N_A}{N_D} + 1 \right) = \frac{q x_n^2 N_D}{2\varepsilon} \left(\frac{N_D}{N_A} + 1 \right)$$

$$x_p^2 = \frac{2\varepsilon(V_{j0} + V_R)}{q N_A \left(\frac{N_A}{N_D} + 1 \right)} \quad x_n^2 = \frac{2\varepsilon(V_{j0} + V_R)}{q N_D \left(\frac{N_D}{N_A} + 1 \right)}$$

$$x_p^2 = \frac{2\varepsilon(V_{j0} + V_R)}{q N_A \left(\frac{N_A}{N_D} + 1 \right)} \quad x_n^2 = \frac{2\varepsilon(V_{j0} + V_R)}{q N_D \left(\frac{N_D}{N_A} + 1 \right)}$$

Para juntas asimétricas:

$$P^+N \longrightarrow x_m = x_n = \left[\frac{2\varepsilon}{q N_D} \right]^{1/2} (V_{j0} + V_R)^{1/2}$$

$$N^+P \longrightarrow x_m = x_p = \left[\frac{2\varepsilon}{q N_A} \right]^{1/2} (V_{j0} + V_R)^{1/2}$$

$$|E_{\max}| = \left[\frac{2q}{\varepsilon} \frac{N_D N_A}{(N_D + N_A)} (V_{j0} + V_R) \right]^{1/2}$$

Capacidad de Juntura

$$C_j = \varepsilon \frac{A}{x_m} \qquad \varepsilon = 1.04 \times 10^{-12} \frac{F}{cm}$$

$$C_j = A \sqrt{\frac{q \varepsilon N_A N_D}{2(N_A + N_D)V_{j0}}} \frac{1}{\sqrt{1 + \frac{V_R}{V_{j0}}}}$$

Para $V_R = 0$ $C_j = C_{j0}$ $C_{j0} = A \sqrt{\frac{q \varepsilon N_A N_D}{2(N_A + N_D)V_{j0}}}$

$$C_j = \frac{C_{j0}}{\sqrt{1 + \frac{V_R}{V_{j0}}}}$$

Capacidad de Juntura

Para calcular C_j supongo una juntura asimétrica P^+N \longrightarrow $x_m = x_n$

$$C_j = \frac{\varepsilon A_E}{\left[\frac{2\varepsilon}{q N_D}\right]^{1/2}} \frac{1}{(V_{j0} + V_R)^{1/2}} = \frac{A_E}{2} \left[\frac{2\varepsilon q N_D}{V_{j0}}\right]^{1/2} \frac{1}{\left(1 + \frac{V_R}{V_{j0}}\right)^{1/2}}$$

Para $V_R = 0 \longrightarrow C_j = C_{j0} = \frac{A_E}{2} \left[\frac{2\varepsilon q N_D}{V_{j0}}\right]^{1/2}$ p/ juntura P^+N

Para $V_R = 0 \longrightarrow C_j = C_{j0} = \frac{A_E}{2} \left[\frac{2\varepsilon q N_A}{V_{j0}}\right]^{1/2}$ p/ juntura N^+P

$$C_j = \frac{C_{j0}}{\left(1 + \frac{V_R}{V_{j0}}\right)^{1/2}}$$